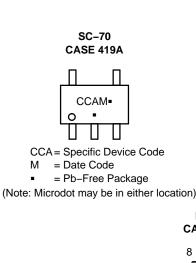
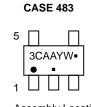
#### MARKING DIAGRAMS





TSOP-5



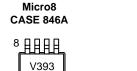


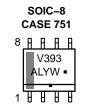
= Assembly Location CA = Specific Device Code M = Date Code

Y = Year W = Work Week • = Pb-Free Package

■ = Pb-Free Package (Note: Microdot may be in either location)

(Note: Microdot may be in either location)





A = Assembly Location Y = Year

W = Work Week
■ Pb-Free Package

(Note: Microdot may be in either location)

AYW=

1 🛮 🖠 🖠 🖠

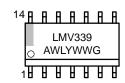
A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week

= Pb-Free Package

TSSOP-14

**CASE 948G** 

#### SOIC-14 CASE 751A



A = Assembly Location WL = Wafer Lot

Y = Year
WW = Work Week
G = Pb-Free Package

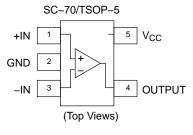
## 

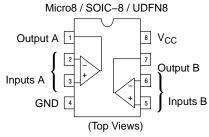
A = Assembly Location

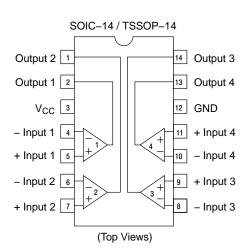
L = Wafer Lot Y = Year W = Work Week • Pb-Free Package

(Note: Microdot may be in either location)

#### **PACKAGE PINOUTS**







#### **MAXIMUM RATINGS**

Symbol	Rating	Value	Unit
V <sub>S</sub>	Voltage on any Pin (referred to V⁻ pin)	5.5	V
$V_{IDR}$	Input Differential Voltage Range	±Supply Voltage	V
$T_J$	Maximum Junction Temperature	150	°C
T <sub>A</sub>	Operating Ambient Temperature Range  LMV331, LMV393, LMV339  NCV331 (Note 3)	-40 to 85 -40 to 125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to 150	°C
$T_L$	Mounting Temperature (Infrared or Convection (1/16" From Case for 30 Seconds))	260	°C
V <sub>ESD</sub>	ESD Tolerance (Note 1) Machine Model Human Body Model	100 1000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage Temperature Range (Note 2)	2.7 to 5.0	V
$\theta_{JA}$	Thermal Resistance SC-70 TSOP-5 Micro8 SOIC-8 UDFN8 SOIC-14 TSSOP-14	280 333 238 212 350 156 190	°C/W

Human Body Model, applicable std. MIL–STD–883, Method 3015.7. Machine Model, applicable std. JESD22–A115–A (ESD MM std. of JEDEC) Field–Induced Charge–Device Model, applicable std. JESD22–C101–C (ESD FICDM std. of JEDEC).
 The maximum power dissipation is a function of T<sub>J(MAX)</sub>, θ<sub>JA</sub>. The maximum allowable power dissipation at any ambient temperature is P<sub>D</sub> = (T<sub>J(MAX)</sub> – T<sub>A</sub>)/<sub>θJA</sub>. All numbers apply for packages soldered directly onto a PC board.
 NCV prefix is qualified for automotive usage.

# **2.7 V DC ELECTRICAL CHARACTERISTICS** (All limits are guaranteed for $T_A = 25^{\circ}C$ , $V^+ = 2.7$ V, $V^- = 0$ V, $V_{CM} = 1.35$ V unless otherwise noted.)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V <sub>IO</sub>			1.7	9	mV
Input Offset Voltage Average Drift	T <sub>C</sub> V <sub>IO</sub>			5		μV/°C
Input Bias Current (Note 4)	Ι <sub>Β</sub>			< 1		nA
Input Offset Current (Note 4)	I <sub>IO</sub>			< 1		nA
Input Voltage Range	V <sub>CM</sub>			0 to 2		V
Saturation Voltage	$V_{SAT}$	I <sub>SINK</sub> ≤ 1 mA		120		mV
Output Sink Current	I <sub>O</sub>	V <sub>O</sub> ≤ 1.5 V	5	23		mA
Supply Current LMV331 NCV331 LMV393 LMV339	I <sub>CC</sub>			40 40 70 140	100 100 140 200	μΑ

## **2.7 V AC ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ , $V^+ = 2.7$ V, $R_L = 5.1$ k $\Omega$ , $V^- = 0$ V unless otherwise noted.)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Propagation Delay – High to Low	t <sub>PHL</sub>	Input Overdrive = 10 mV Input Overdrive = 100 mV		1000 500		ns
Propagation Delay – Low to High	t <sub>PLH</sub>	Input Overdrive = 10 mV Input Overdrive = 100 mV		800 200		ns

<sup>4.</sup> Guaranteed by design and/or characterization.

**5.0 V DC ELECTRICAL CHARACTERISTICS** (All limits are guaranteed for  $T_A = 25$ °C,  $V^+ = 5$  V,  $V^- = 0$  V,  $V_{CM} = 2.5$  V unless otherwise noted. Limits over temperature are guaranteed by design and/or characterization.)

Parameter	Symbol	Condition (Note 6)	Min	Тур	Max	Unit
Input Offset Voltage	$V_{IO}$	$T_A = T_{LO}$ to $T_{HIGH}$		1.7	9	mV
Input Offset Voltage Average Drift		$T_A = T_{LO}$ to $T_{HIGH}$		5		μV/°C
Input Bias Current (Note 5)	Ι <sub>Β</sub>	$T_A = T_{LO}$ to $T_{HIGH}$		< 1		nA
Input Offset Current (Note 5)	I <sub>IO</sub>	$T_A = T_{LO}$ to $T_{HIGH}$		< 1		nA
Input Voltage Range	V <sub>CM</sub>			0 to 4.2		V
Voltage Gain (Note 5)	$A_V$		20	50		V/mV
Saturation Voltage	V <sub>SAT</sub>	$I_{SINK} = 10 \text{ mA}$ $T_A = T_{LO} \text{ to } T_{HIGH}$		200	400 700	mV
Output Sink Current	ΙO	V <sub>O</sub> ≤ 1.5 V	10	84		mA
Supply Current LMV331	Icc	$T_A = T_{LO}$ to $T_{HIGH}$		60	120 150	μΑ
Supply Current LMV393	Icc	T <sub>A</sub> = T <sub>LO</sub> to T <sub>HIGH</sub>		100	200 250	μΑ
Supply Current LMV339	Icc	$T_A = T_{LO}$ to $T_{HIGH}$		170	300 350	μΑ
Output Leakage Current (Note 5)		$T_A = T_{LO}$ to $T_{HIGH}$		0.003	1	μΑ

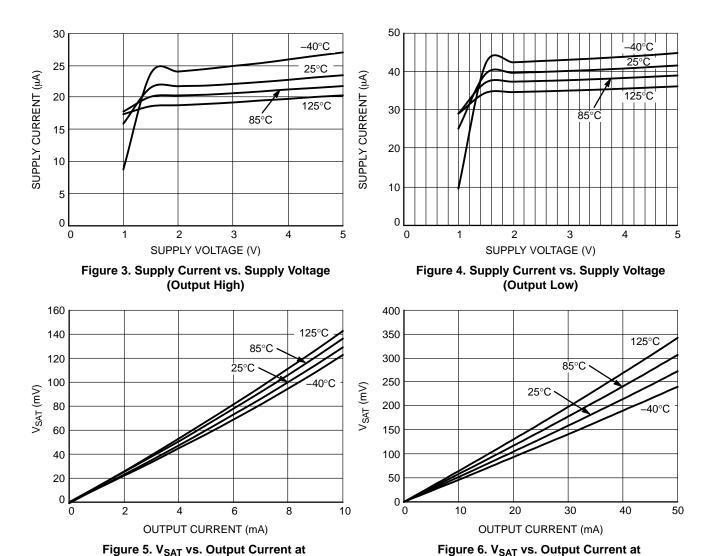
### **5.0 V AC ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ , $V^+ = 5$ V, $R_L = 5.1$ k $\Omega$ , $V^- = 0$ V unless otherwise noted.)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Propagation Delay – High to Low	t <sub>PHL</sub>	Input Overdrive = 10 mV Input Overdrive = 100 mV		1500 900		ns
Propagation Delay – Low to High	t <sub>PLH</sub>	Input Overdrive = 10 mV Input Overdrive = 100 mV		800 200		ns

 <sup>5.</sup> Guaranteed by design and/or characterization.
 6. For LMV331, LMV393, LMV339: T<sub>A</sub> = -40°C to 85°C For NCV331: T<sub>A</sub> = -40°C to 125°C

#### **TYPICAL CHARACTERISTICS**

 $(V_{CC} = 5.0 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 5 \text{ k}\Omega \text{ unless otherwise specified})$ 



 $V_{CC} = 5.0 V$ 

 $V_{CC} = 2.7 \text{ V}$ 

## NEGATIVE TRANSITION INPUT – $V_{CC} = 2.7 \text{ V}$

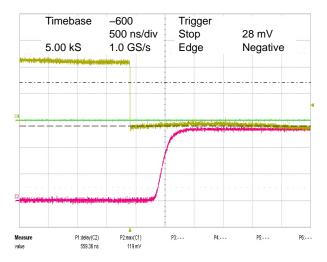


Figure 7. 10 mV Overdrive

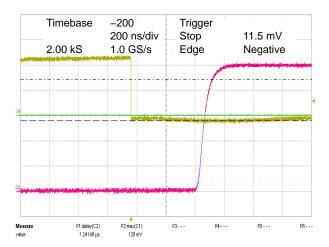


Figure 8. 20 mV Overdrive

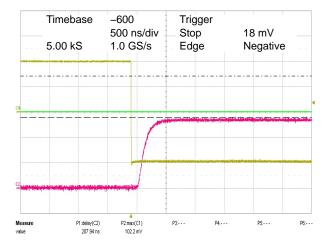


Figure 9. 100 mV Overdrive

## POSITIVE TRANSITION INPUT – $V_{CC} = 2.7 \text{ V}$

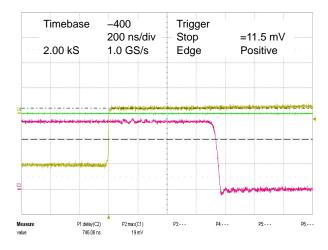


Figure 10. 10 mV Overdrive

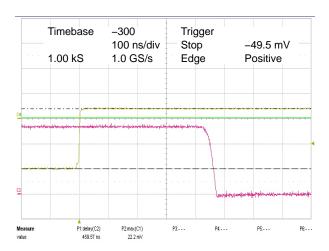


Figure 11. 20 mV Overdrive

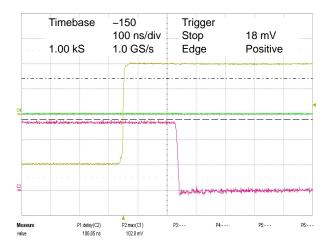


Figure 12. 100 mV Overdrive

## NEGATIVE TRANSITION INPUT – $V_{CC} = 5.0 \text{ V}$

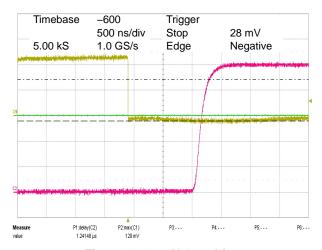


Figure 13. 10 mV Overdrive

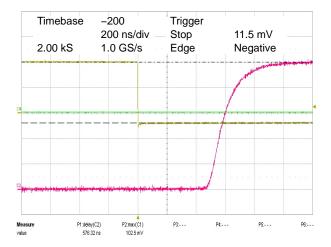


Figure 14. 20 mV Overdrive

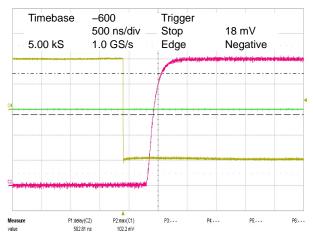


Figure 15. 100 mV Overdrive

## POSITIVE TRANSITION INPUT – $V_{CC} = 5.0 \text{ V}$

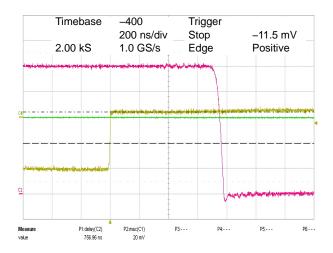


Figure 16. 10 mV Overdrive

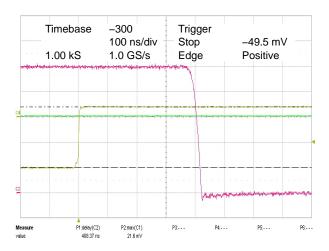


Figure 17. 20 mV Overdrive

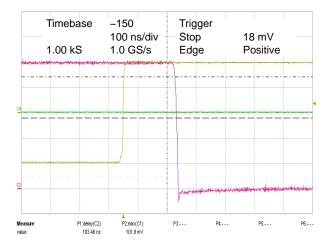


Figure 18. 100 mV Overdrive

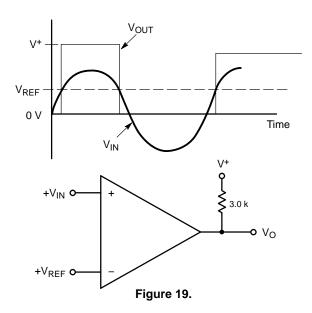
#### **APPLICATION CIRCUITS**

#### **Basic Comparator Operation**

The basic operation of a comparator is to compare two input voltage signals, and produce a digital output signal by determining which input signal is higher. If the voltage on the non–inverting input is higher, then the internal output transistor is off and the output will be high. If the voltage on the inverting input is higher, then the output transistor will be on and the output will be low. The LMV331/393/339 has an open–drain output stage, so a pull–up resistor to a positive supply voltage is required for the output to switch properly.

The size of the pull–up resistor is recommended to be between 1 k $\Omega$  and 10 k $\Omega$ . This range of values will balance two key factors; i.e., power dissipation and drive capability for interface circuitry.

Figure 19 illustrates the basic operation of a comparator and assumes dual supplies. The comparator compares the input voltage  $(V_{IN})$  on the non–inverting input to the reference voltage  $(V_{REF})$  on the inverting input. If  $V_{IN}$  is less than  $V_{REF}$ , the output voltage  $(V_O)$  will be low. If  $V_{IN}$  is greater than  $V_{REF}$ , then  $V_O$  will be high.

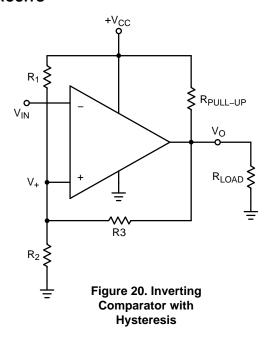


#### Comparators and Stability

A common problem with comparators is oscillation due to their high gain. The basic comparator configuration in Figure 19 may oscillate if the differential voltage between the input pins is close to the device's offset voltage. This can happen if the input signal is moving slowly through the comparator's switching threshold or if unused channels are connected to the same potential for termination of unused channels. One way to eliminate output oscillations or 'chatter' is to include external hysteresis in the circuit design.

#### **Inverting Configuration with Hysteresis**

An inverting comparator with hysteresis is shown in Figure 20.



When  $V_{IN}$  is less than the voltage at the non–inverting node,  $V_+$ , the output voltage will be high. When  $V_{IN}$  is greater than the voltage at  $V_+$ , then the output will be low. The hysteresis band (Figure 21) created from the resistor network is defined as:

$$\Delta V_{+} = V_{T1} - V_{T2}$$

where  $V_{T1}$  and  $V_{T2}$  are the lower and upper trip points, respectively.

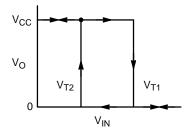


Figure 21.

 $V_{T1}$  is calculated by assuming that the output of the comparator is pulled up to supply when high. The resistances  $R_1$  and  $R_3$  can be viewed as being in parallel which is in series with  $R_2$  (Figure 22). Therefore  $V_{T1}$  is:

$$V_{T1} = \frac{V_{CC} R_2}{(R_1 \parallel R_3) + R_2}$$

 $V_{T2}$  is calculated by assuming that the output of the comparator is at ground potential when low. The resistances  $R_2$  and  $R_3$  can be viewed as being in parallel which is in series with  $R_1$  (Figure 23). Therefore  $V_{T2}$  is:

$$V_{T2} = \frac{V_{CC}(R_2 \| R_3)}{R_1 + (R_2 \| R_3)}$$

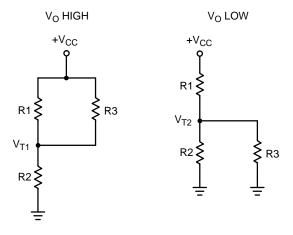


Figure 22.

Figure 23.

#### Non-inverting Configuration with Hysteresis

A non-inverting comparator is shown in Figure 24.

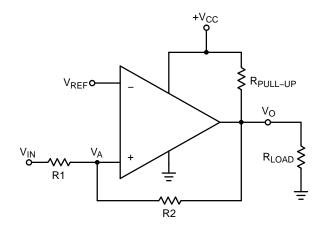


Figure 24.

The hysteresis band (Figure 25) of the non–inverting configuration is defined as follows:

$$\Delta V_{in} = V_{CC}R_1/R_2$$

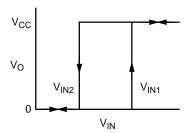


Figure 25.

When  $V_{IN}$  is much less than the voltage at the inverting input ( $V_{REF}$ ), then the output is low.  $R_2$  can then be viewed as being connected to ground (Figure 26). To calculate the voltage required at  $V_{IN}$  to trip the comparator high, the following equation is used:

$$V_{in1} = \frac{V_{ref} (R_1 + R_2)}{R_2}$$

When the output is high,  $V_{IN}$  must less than or equal to  $V_{REF}$  ( $V_{IN} \leq V_{REF}$ ) before the output will be low again (Figure 27). The following equation is used to calculate the voltage at  $V_{IN}$  to switch the output back to the low state:

$$V_{in2} = \frac{V_{ref} (R_1 + R_2) - V_{CC} R_1}{R_2}$$

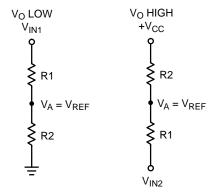


Figure 26.

Figure 27.

#### **Termination of Unused Inputs**

Proper termination of unused inputs is a good practice to keep the output from 'chattering.' For example, if one channel of a dual or quad package is not being used, then the inputs must be connected to a defined state. The recommended connections would be to tie one input to  $V_{CC}$  and the other input to ground.

### **ORDERING INFORMATION**

Order Number	Number of Channels	Specific Device Marking	Package Type	Shipping <sup>†</sup>
LMV331SQ3T2G	Single	CCA	SC-70 (Pb-Free)	3000 / Tape & Reel
LMV331SN3T1G	Single	3CA	TSOP-5 (Pb-Free)	3000 / Tape & Reel
NCV331SN3T1G	Single	3CA	TSOP-5 (Pb-Free)	3000 / Tape & Reel
LMV393DMR2G	Dual	V393	Micro8 (Pb-Free)	4000 / Tape & Reel
LMV393DR2G	Dual	V393	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LMV393MUTAG	Dual	CA	UDFN8 (Pb-Free)	3000 / Tape & Reel
LMV339DR2G	Quad	LMV339	SOIC-14 (Pb-Free)	2500 / Tape & Reel
LMV339DTBR2G	Quad	LMV 339	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*Contact factory.



#### SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE L**

**DATE 17 JAN 2013** 



- TES:
  DIMENSIONING AND TOLERANCING
  PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  419A-01 OBSOLETE. NEW STANDARD 3.
- 419A-02.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



## 0.50 0.0197 0.65 0.025 0.65 0.025 0.40 0.0157 1.9 mm 0.0748 SCALE 20:1

**SOLDER FOOTPRINT** 

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4

5. COLLECTOR	5. CATHODE	5. CATHODE I	5. GATE 2	5. CATHODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

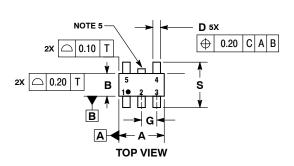
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DESCRIPTION:	SC-88A (SC-70-5/SOT-35	63)	PAGE 1 OF 1		

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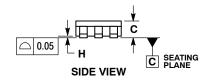


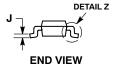
TSOP-5 **CASE 483 ISSUE N** 

**DATE 12 AUG 2020** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE
  MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
C	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2 50	3.00		

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code = Year = Pb-Free Package

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

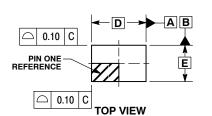
DOCUMENT NUMBER:	98ARB18753C	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	TSOP-5		PAGE 1 OF 1

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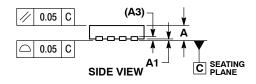
SCALE 4:1

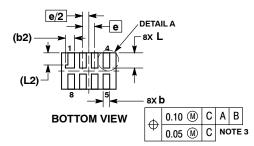


**DATE 08 NOV 2006** 

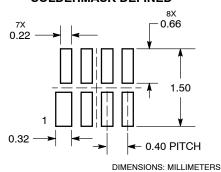








#### **MOUNTING FOOTPRINT SOLDERMASK DEFINED**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSION & APPLIES TO PLATED
- DINICIPION D APPLIES TO PLATED
  TERMINAL AND IS MEASURED BETWEEN
  0.15 AND 0.30 mm FROM TERMINAL TIP.
  MOLD FLASH ALLOWED ON TERMINALS
  ALONG EDGE OF PACKAGE, FLASH MAY
  NOT EXCEED 0.03 ONTO BOTTOM
  SURFACE OF TERMINALS.
  DETAIL A SHOWS ODTIONAL
- DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.127	REF	
b	0.15	0.25	
b2	0.30	REF	
D	1.80	BSC	
E	1.20	BSC	
е	0.40	BSC	
L	0.45	0.55	
L1	0.00	0.03	
L2	0.40 REF		

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	UDFN8 1.8X1.2. 0.4P	•	PAGE 1 OF 1

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SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

MILLIMETERS		MILLIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

## DATE 16 FEB 2011

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1  STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE  STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. PINS 2	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1  STYLE 7: PIN 1. IMPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2	3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd  STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. SOURCE 2. SOURCE
6. BIAS 2 7. INPUT 8. GROUND	5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15:  PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		
	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 9. COMMON CATHODE/VCC 9. COMMON CATHODE/VCC 1. I/O LINE 1 2. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 5 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. I/O LINE 5 8. COMMON ANODE/GND 8. SOURCE 9. II. ILIMIT 9. SOURCE 1. SOURCE 1. SOURCE 1. SOURCE 2. SOURCE 1 2. SOURCE 1 3. GATE 2 4. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. CATHODE, COMMON 8. N-DRAIN 8. CATHODE, COMMON 8. CATHODE 9IN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 4. GATE 2 5. DRAIN 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 8. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. (/O LINE 1 2. COMMON CATHODE/VCC 1. (/O LINE 3 5. COMMON ANODE/GND 6. (/O LINE 4 7. (/O LINE 5 8. COMMON ANODE/GND 8. LINE 2 OUT 9. COMMON ANODE/GND 8. LINE 1 OUT  STYLE 26: PIN 1. GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 27: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 28: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMM

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DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

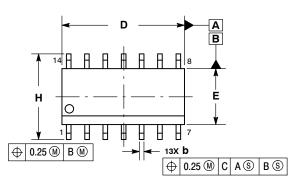
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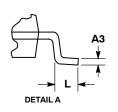


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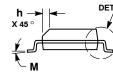
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





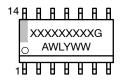




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***



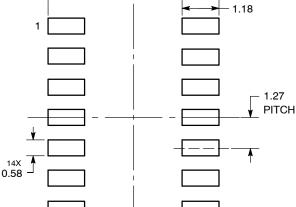
XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

## - 6.50 -14X

**SOLDERING FOOTPRINT\*** 



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### SOIC-14 CASE 751A-03 ISSUE L

### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

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#### Micro8 CASE 846A-02 ISSUE K

**DATE 16 JUL 2020** 









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



MOUNTING FOOTPRINT

DIM	MI	MILLIMETERS		
ויונע	MIN.	N□M.	MAX.	
Α	-	-	1.10	
A1	0.05	0.08	0.15	
b	0.25	0.33	0.40	
c	0.13	0.18	0.23	
D	2.90	3.00	3.10	
Ε	2.90	3.00	3.10	
е	0.65 BSC			
HE	4.75	4.90	5.05	
L	0.40	0.55	0.70	

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

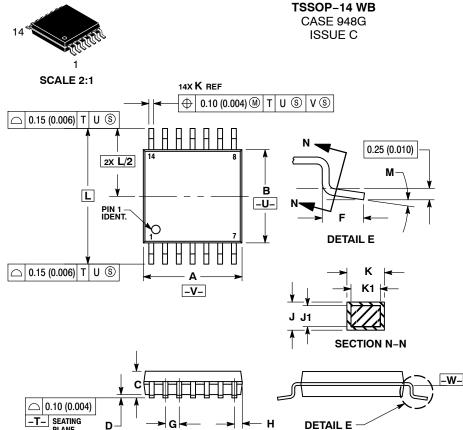
(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
<ol><li>SOURCE</li></ol>	2. GATE 1	2. N-GATE
<ol><li>SOURCE</li></ol>	3. SOURCE 2	3. P-SOURCE
<ol><li>GATE</li></ol>	4. GATE 2	4. P-GATE
<ol><li>DRAIN</li></ol>	5. DRAIN 2	5. P-DRAIN
<ol><li>DRAIN</li></ol>	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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DESCRIPTION:	MICRO8		PAGE 1 OF 1

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8 °	0 °	8 °

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

◀	7.06
1	
	<del> </del>
	0.65
, <u> </u>	<b>— — —</b> • • • • • • • • • • • • • • • • • • •
14X	<b>─</b>
0.36 14X 1.26	DIMENSIONS: MILLIMETERS

**SOLDERING FOOTPRINT** 

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